

Abstract of the Disclosure

The present invention relates to a method for forming a multi-transmittance phase-shifting mask for the manufacture of
5 highly integrated semiconductor devices in which portions of a plurality of light blocking layers are selectively removed to modify the transmittance of various regions of the mask and suppress undesired patterns, such as ghost images and side lobe effects to permit increased integration levels and
10 improved yield in the production of the semiconductor devices.

03/22/2014 06:25:01